

600V N-CHANNEL ENHANCEMENT MODE MOSFET

MAIN CHARACTERISTICS

I_D	35A
V_{DSS}	600V
$R_{DS(ON)-typ}(@V_{GS}=10V)$	<0.15Ω (Type:0.13Ω)

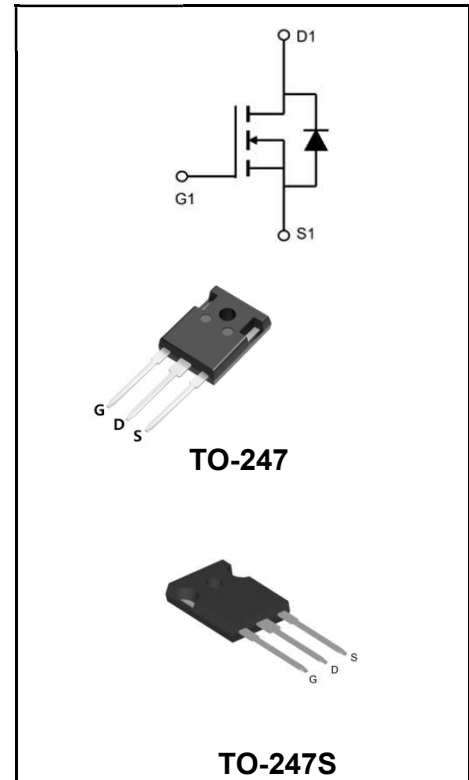
Features

- ◆Fast Switching
- ◆Low ON Resistance
- ◆Low Gate Charge
- ◆100% Single Pulse avalanche energy Test
- ◆LeadfreeincomplywithEUroHS2011/65/EUdirectives



Mechanical Data

- ◆Case: Molded plastic
- ◆Mounting Position: Any
- ◆Molded Plastic: UL Flammability Classification Rating 94V-0
- ◆Solder bath temperature275°C maximum,10s per JESD22-106



Product Specification Classification

Part Number	Package	Marking	Pack
YFW35N60AP	TO-247	YFW 35N60AP XXXXX	30PCS/Tube
YFW35N60APS	TO-247S	YFW 35N60APS XXXXX	30PCS/Tube

Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Symbols	Value	Units
		247/247S	
Drain-Source Voltage	V_{DS}	600	V
Gate-Source Voltage	V_{GS}	±30	V
Continue Drain Current	I_D	35	A
-Continuous (TC = 100°C)		24	
Pulsed Drain Current (Note1)	I_{DM}	110	A
Power Dissipation	P_D	240	W
-Derate above 25°C		1.2	
Single Pulse Avalanche Energy (Note2)	E_{AS}	1800	mJ
Avalanche Current (Note 1)	I_{AR}	35	A
Repetitive Avalanche Energy (Note 1)	E_{AS}	43	mJ
Operating Temperature Range	T_J	150	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C
Thermal Resistance, Junction to Case	R_{θJC}	0.4	°C/W
Thermal Resistance, Junction to Ambient	R_{θJA}	42	°C/W

Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	BV_{DSS}	600	-	-	V
Breakdown Voltage Temperature Coefficient	I _D =250μA (Referenced to 25°C)	$\frac{\Delta BV_{DSS}}{\Delta T_J}$	-	0.65	-	V/°C
Drain-Source Leakage Current	V _{DS} = 600 V, V _{GS} = 0 V	I_{DSS}	-	-	1	uA
	V _{DS} = 480 V, T _c = 125°C		-	-	10	
Gate Leakage Current	V _{GS} = ± 30 V, V _{DS} = 0 V	I_{GSS}	-	-	±100	nA
Gate-Source Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	V_{GS(th)}	3	-	5	V
Drain-Source On-State Resistance	V _{GS} = 10 V, I _D = 17.5A	R_{DS(on)}	-	0.13	0.15	Ω
Forward Transconductance	V _{DS} = 15 V, I _D = 17.5 A	g_{fs}	-	27.6	-	S
Input Capacitance	V _{GS} = 0 V, V _{DS} = 25 V, f = 1MHz	C_{iss}	-	4921	-	pF
Output Capacitance		C_{OSS}	-	2312	-	
Reverse Transfer Capacitance		C_{rss}	-	135	-	
Turn-on Delay Time	I _D = 35, V _{DD} = 300V, R _G =10Ω(Note3,4)	td(ON)	-	34	-	nS
Rise Time		tr	-	121	-	
Turn-Off Delay Time		td(OFF)	-	106	-	
Fall Time		tf	-	72	-	
Total Gate Charge	I _D =35 A, V _{DD} = 480 V, V _{GS} = 10 V(Note3,4)	Q_G	-	138	-	nC
Gate to Source Charge		Q_{GS}	-	32	-	
Gate to Drain Charge		Q_{GD}	-	70	-	

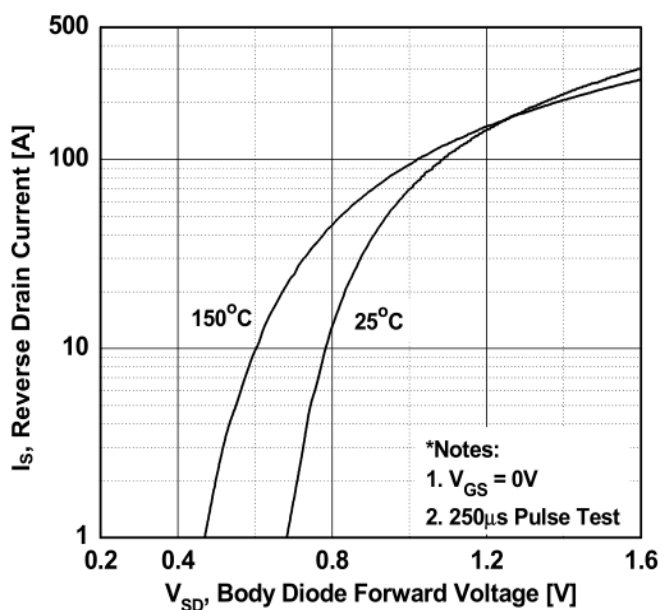
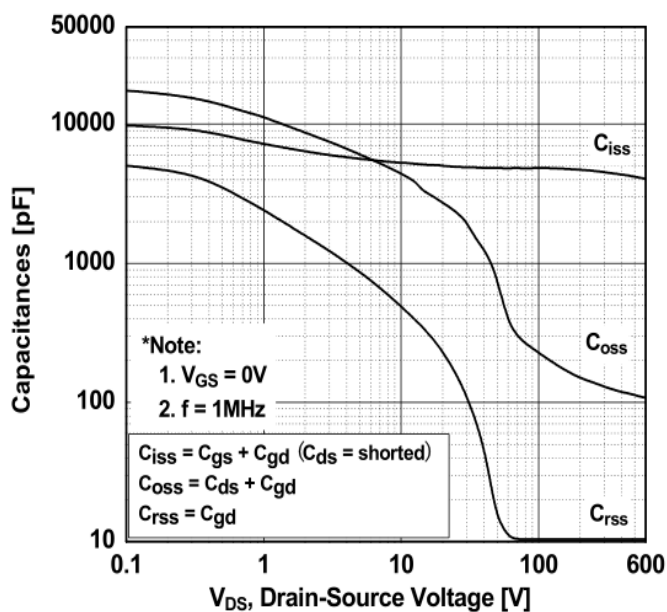
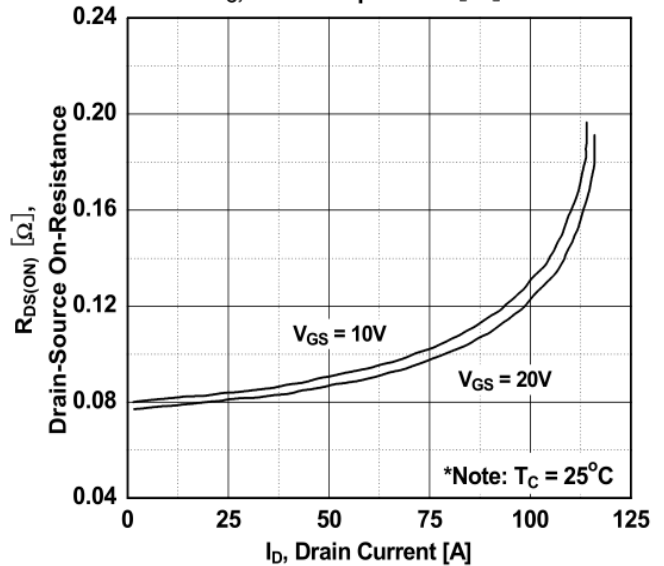
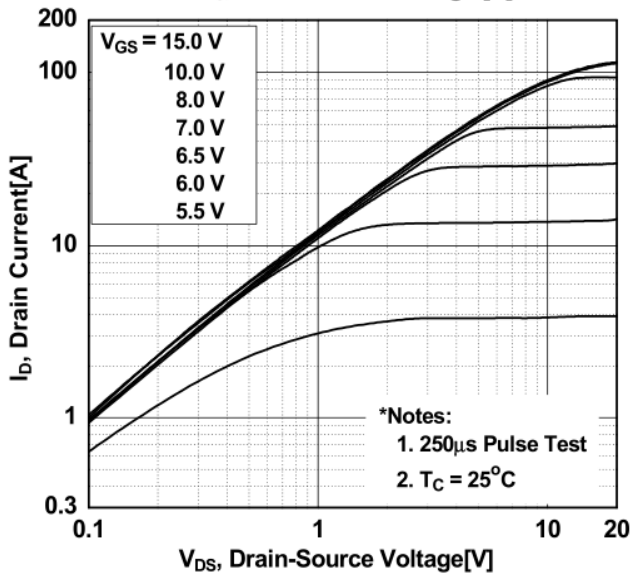
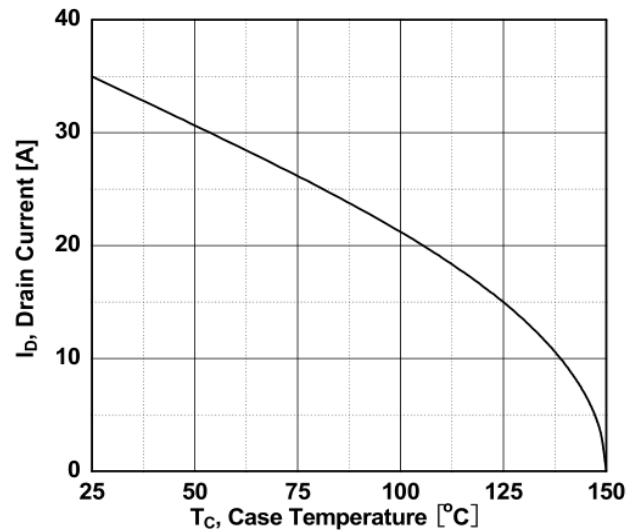
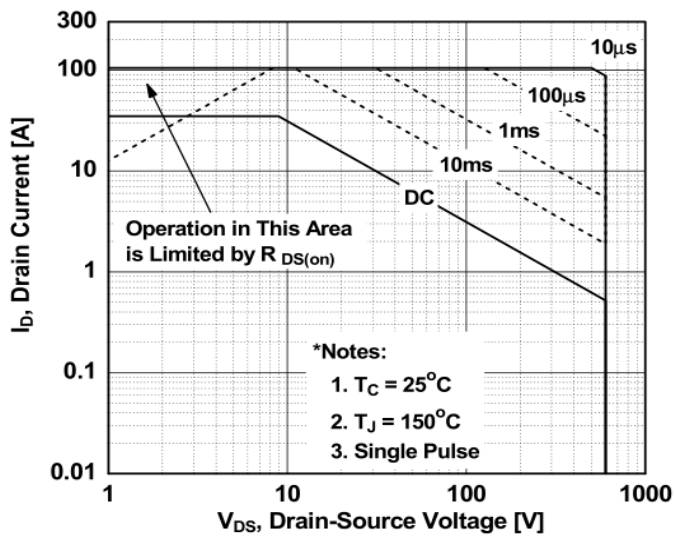
Source-Drain Diode Characteristics at Ta=25°C unless otherwise specified

Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
Maximun Body-Diode Continuous Current		I_S	-	-	35	A
Maximun Body-Diode Pulsed Current		I_{SM}	-	-	110	A
Drain-Source Diode Forward Voltage	I _{SD} =35A	V_{SD}	-	-	1.4	V
Reverse Recovery Time	I _{SD} = 35A, V _{GS} = 0 V, dI _F / dt = 100 A/μs	trr	-	613	-	nS
Reverse Recovery Charge		Qrr	-	15.8	-	uC

Note:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. IAS = 35 A, VDD = 50 V, L =3mH, RG = 25Ω, starting TJ = 25°C.
3. ulse test: Pulse Width ≤300 μ s, Duty Cycle≤2%.
4. Essentially Independent of Operating Temperature.

Ratings and Characteristic Curves



Package Outline Dimensions Millimeters

TO-247

	Dim.	Min.	Max.
	A	15	16
	B	20	21
	C	41	42
	D	5	6
	E	4	5
	F	2.5	3.5
	G	1.75	2.5
	H	3	3.5
	I	8	10
	J	4.9	5.1
	K	1.9	2.1
L	3.5	4	
M	4.75	5.25	
N	2	3	
O	0.55	0.75	
P	Typ 5.08		
Q	1.2	1.3	
All Dimensions in millimeter			

TO-247S

	Dim.	Min.	Max.
	A	15	16
	B	19.5	20.5
	C	33.5	35.5
	D	5	6
	E	3.5	4.5
	F	2.5	3.5
	G	1.75	2.5
	H	3	4
	I	9	11
	J	4.9	5.1
	K	1	1.3
L	3.75	4.25	
M	4.75	5.25	
N	1.8	2.2	
O	0.45	0.6	
P	Typ 5.08		
Q	1.2	1.3	
All Dimensions in millimeter			